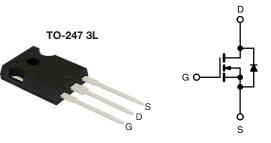


MaxSiC™ 1200 V N-Channel SiC MOSFET

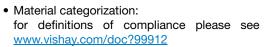


N-Channel MOSFET

Marking Code: 120A080FW

FEATURES

- · Fast switching speed
- Short circuit withstand time 3 µs





APPLICATIONS

- Charger
- · Auxiliary motor drive
- DC/DC converter

PRODUCT SUMMARY				
V _{DS} (V) at T _J max.	1200			
R _{DS(on)} typ. (mΩ) at 25 °C	V _{GS} = 20 V 80			
Q _g typ. (nC)	47.3			
I _D (A)	29			
C _{oss} typ. (pF)	50			
P _D (W)	139			
Configuration	Single			

ORDERING INFORMATION	
Package	TO-247 3L
Lead (Pb)-free and halogen-free	MXP120A080FW-GE3

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage ^a		V _{DS}	1200		
Gate-source voltage		V_{GS}	-10 / +22	V	
Recommended operation voltage of gate-source		V_{GSOP}	-5 / +20	i	
Continuous drain current	T _C = 25 °C	I _D	29		
	T _C = 100 °C	I _D	18	Α	
Pulsed drain current ^b		I _{DM}	58	I	
Short-circuit withstand time c		T _{SC}	3	μs	
Maximum power dissipation	T _C = 25 °C	P_D	139	- w	
	T _C = 100 °C	P_{D}	56		
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +150	°C	
Soldering recommendations (peak temperature)	For 10 s		260	°C	

Notes

- a. $T_J = 25$ °C to 150 °C
- b. Repetitive rating; pulse width limited by maximum junction temperature
- c. Verified by the design / characterization



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THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R_{thJA}	-	40	°C/W
Maximum junction-to-case (drain)	R_{thJC}	-	0.9	G/ VV

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 1 \text{ mA}$	1200	-	-	V	
Onto a surrent bound by a let us (A1)	V	$V_{DS} = V_{GS}$, $I_D = 5 \text{ mA}$	-	2.69	-	V	
Gate-source threshold voltage (N)	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 5 \text{ mA}, T_J = 150 \text{ °C}$	-	1.86	-	V	
Gate-source leakage		V _{GS} = +22 V, V _{DS} = 0 V	-	-	100	nA	
	I _{GSS}	V _{GS} = -10 V, V _{DS} = 0 V	-	-	-100		
Zero gate voltage drain current	I _{DSS}	V _{DS} = 960 V, V _{GS} = 0 V	-	-	10	μΑ	
		V _{GS} = 20 V, I _D = 20 A	-	80	100		
Duning and an adult and advantage	Б	V _{GS} = 20 V, I _D = 20 A, T _J = 150 °C	-	128	160	0	
Drain-source on-state resistance	R _{DS(on)}	V _{GS} = 18 V, I _D = 20 A	-	95	119	- mΩ	
		V _{GS} = 18 V, I _D = 20 A, T _J = 150 °C	-	140	175		
Dynamic							
Input capacitance	C _{iss}		-	1156	-	pF	
Output capacitance	C _{oss}	V 0.V.V 900.V.f 1.MI.I-	-	50	-		
Reverse transfer capacitance	C _{rss}	$V_{GS} = 0 \text{ V}, V_{DS} = 800 \text{ V}, f = 1 \text{ MHz}$	-	5	-		
Coss Stored Energy	E _{oss}		_	20	-	μJ	
Total gate charge	Q_g		-	47.3	-	nC	
Gate-source charge	Q_{gs}	$V_{GS} = 18 \text{ V}, I_D = 20 \text{ A}, V_{DS} = 800 \text{ V}$	-	14.2	-		
Gate-drain charge	Q_{gd}		_	17.8	-		
Gate Resistance	R _g	V _{DS} = 0 V, f = 1 MHz	-	9.8	-	Ω	
Switching Characteristics							
Turn-on delay time	t _{d(on)}		-	25.6	-		
Rise time	t _r		_	15.6	-		
Turn-off delay time	t _{d(off)}	$V_{GS} = -5 \text{ V} \sim 18 \text{ V}, I_D = 20 \text{ A},$	-	16	-	ns	
Fall time	t _f	$V_{DS} = 800 \text{ V}, R_{g(ext)} = 4.4 \Omega$	_	9	-		
Turn-on switching energy	E _{on}		-	386	-	1	
Turn-off switching energy	E _{off}		-	37	-	μJ	
Body Diode Ratings and Characteristi							
Forward diode voltage	V_{SD}	V _{GS} = -5 V, I _{SD} = 10 A, T _J = 25 °C	-	5.1	-	V	
Continuous diode forward current	I _{SD}	V 5V T 05 °C	-	-	21	Λ.	
Pulsed diode forward current	I _{SDM}	V _{GS} = -5 V, T _J = 25 °C	-	-	58	A	
Reverse recovery time	t _{rr}		-	14	-	ns	
Reverse recovery charge	Q _{rr}	$V_{GS} = -5 \text{ V}, I_{SD} = 20 \text{ A},$ $V_{B} = 800 \text{ V}, \text{ di/dt} = 1000 \text{ A/}\mu\text{s}$	-	35	-	nC	
Reverse recovery current	I _{rrm}	V _R = 600 V, αι/αι = 1000 A/μS	-	4.5	-	Α	

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

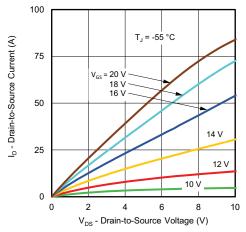


Fig. 1 - Typical Output Characteristics

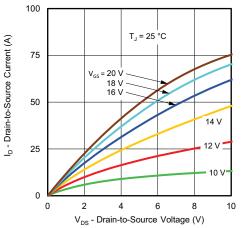


Fig. 2 - Typical Output Characteristics

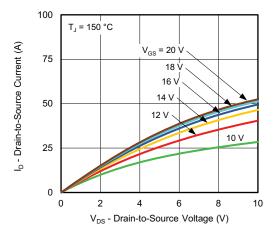


Fig. 3 - Typical Output Characteristics

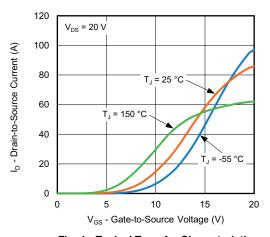


Fig. 4 - Typical Transfer Characteristics

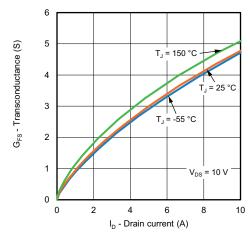


Fig. 5 - Forward Transconductance vs. Drain Current

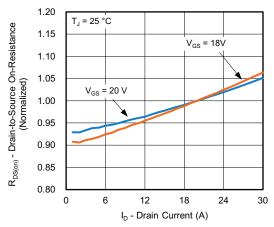


Fig. 6 - Normalized On-Resistance vs. Drain Current



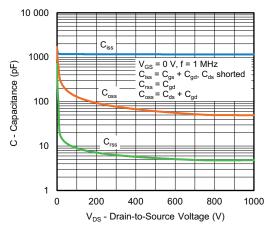


Fig. 7 - Typical Capacitance vs. Drain-to-Source Voltage

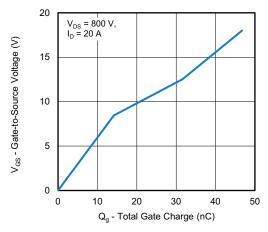


Fig. 8 - Typical Gate Charge vs. Gate-to-Source Voltage

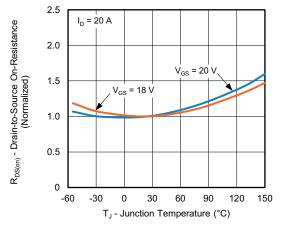


Fig. 9 - Normalized On-Resistance vs. Temperature

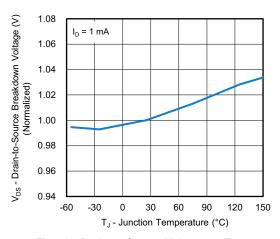


Fig. 10 - Drain-to-Source Voltage vs. Temperature

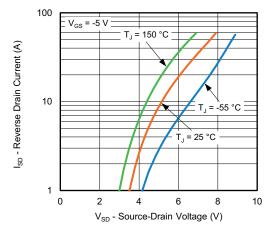


Fig. 11 - Typical Source-Drain Diode Forward Voltage

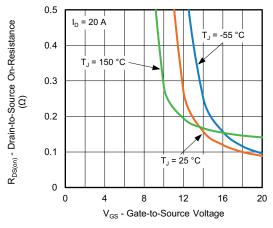


Fig. 12 - On-Resistance vs. Gate-to-Source Voltage

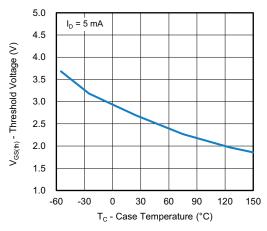


Fig. 13 - Threshold Voltage vs. Case Temperature

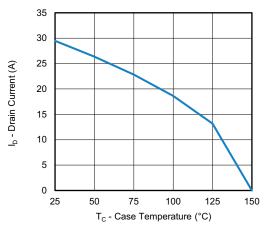


Fig. 14 - Drain Current vs. Case Temperature

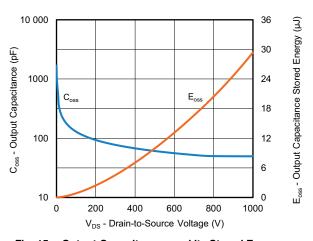


Fig. 15 - Output Capacitances and its Stored Energy vs.

Drain-to-Source Voltage

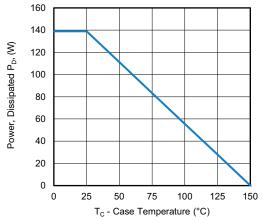


Fig. 16 - Power, Dissipated P_D vs. Case Temperature

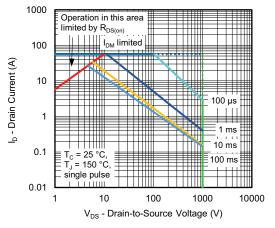


Fig. 17 - Safe Operating Area

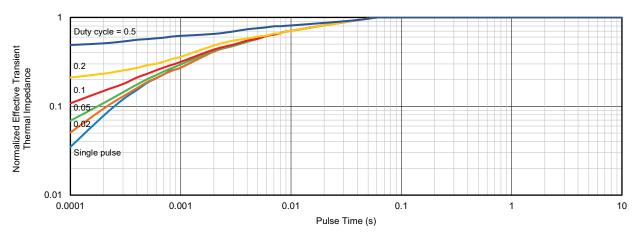


Fig. 18 - Normalized Effective Transient Thermal Impedance



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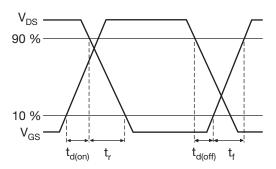


Fig. 19 - Waveforms of Switching Time

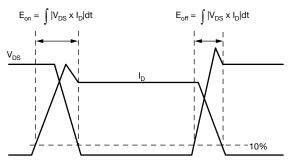


Fig. 20 - Waveforms for Switching Energy

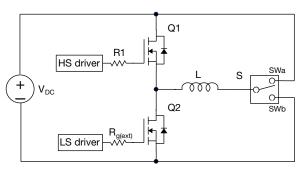


Fig. 21 - Switching and Reverse Diode Characteristics Measurement Circuit

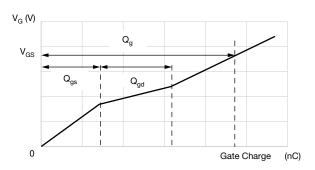


Fig. 22 - Waveforms for Gate Charge

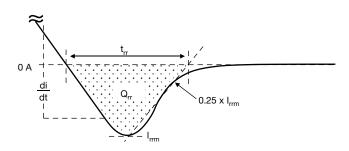


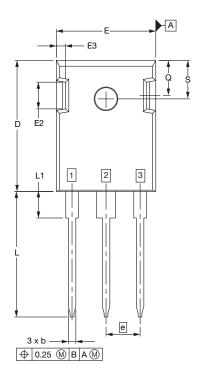
Fig. 23 - Waveforms for Reverse Recovery

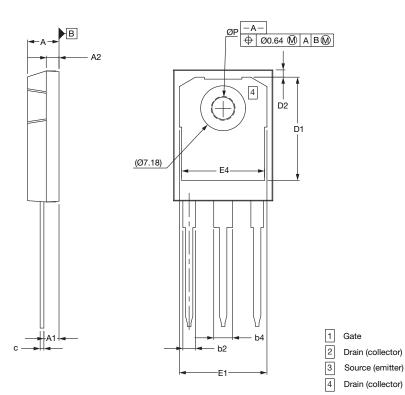
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Case Outline for TO-247AD 3L

FACILITY CODE: N





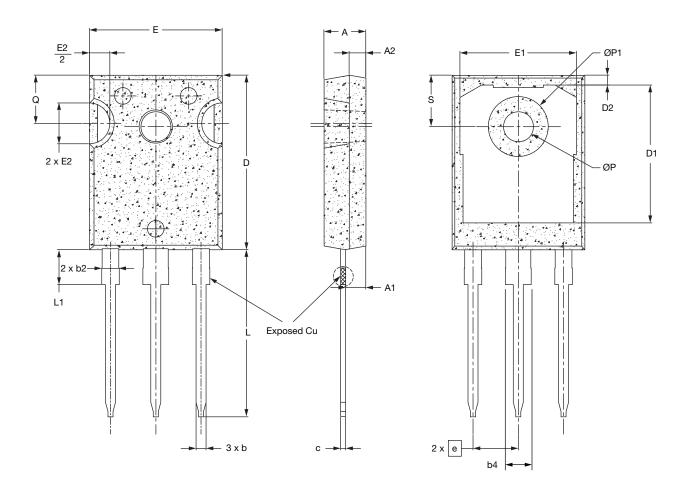
DIM.	MILLIMETERS		
DIIVI.	MIN.	MAX.	
A	4.83	5.21	
A1	2.29	2.54	
A2	1.91	2.16	
b	1.07	1.33	
b2	1.91	2.41	
b4	2.87	3.38	
С	0.55	0.68	
D	20.80	21.10	
D1	16.25	17.65	
D2	0.95	1.25	
Е	15.75	16.13	
E1	13.10	14.15	
E2	3.68	5.10	
E3	1.00	1.90	
E4	12.38	13.43	
е	5.44	BSC.	
N	3	3	
L	19.81	20.32	
L1	4.10	4.40	
ØP	3.51	3.65	
Q	5.49	6.00	
S	6.04	6.30	

Notes

- All metal surfaces: tin plated (MATTE), except area of cut Dimensioning and toleranceing confirm to ASME Y14.5M-1994
- All dimensions are in millimeters
- This drawing will meet all dimensions requirement of JEDEC outlines TO-247 AD



FACILITY CODE: 9







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DIM		MILLIMETERS			
DIM.	MIN.	NOM.	MAX.		
Α	4.83	5.02	5.21		
A1	2.29	2.41	2.55		
A2	1.50	2.00	2.49		
b	1.12	1.20	1.33		
b2 ⁽¹⁾	1.91	2.00	2.39		
b4 ⁽¹⁾	2.87	3.00	3.22		
С	0.55	0.60	0.69		
D (2)	20.80	20.95	21.10		
D1 ⁽³⁾	16.25	16.55	17.65		
D2	0.51	1.19	1.35		
E (2)	15.75	15.94	16.13		
E1 ⁽³⁾	13.46	14.02	14.16		
E2	4.32	4.91	5.49		
е	5.44 BSC.				
L	19.81	20.07	20.32		
L1 ⁽⁴⁾	4.10	4.19	4.40		
ØP ⁽⁵⁾	3.56	3.61	3.65		
ØP1	7.19 ref.				
Q	5.39	5.79	6.20		
S	6.04	6.17	6.30		
ECNI E24 0220 Pay A 12 May 200	24	•			

ECN: E24-0229-Rev. A, 13-May-2024

DWG: 6118

Notes

- Package reference: JEDEC TO-247, variation AD
- All dimensions are in mm
- Slot required, notch may be rounded
- (1) Dimension b2 and b4 does not include dambar protrusion
- (2) Dimension D and E do not include mold flash
- (3) Thermal pad contour optional within dimension D1 and E1
- (4) Lead Finish Uncontrolled In L1
- $^{(5)}$ ØP to have a draft angle of 1.5 $^{\circ}$ ref. to the top of the part with hole diameter of 3.91mm



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